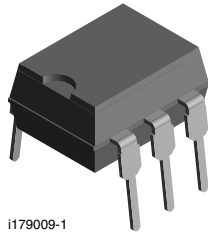
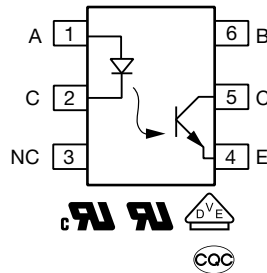


## Optocoupler, Phototransistor Output, no Base Connection



i179009-1



### FEATURES

- Isolation test voltage, 5300 V<sub>RMS</sub>
- No base terminal connection for improved common mode interface immunity
- Long term stability
- Industry standard dual in line package
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### LINKS TO ADDITIONAL RESOURCES



3D Models



Design Tools



Related Documents



Models



Footprints



Schematics

### AGENCY APPROVALS

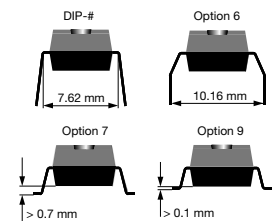
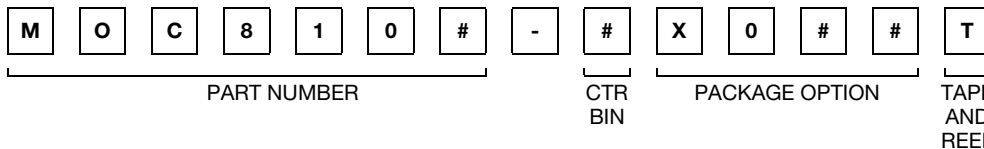
- [UL](#)
- [cUL](#)
- [DIN EN 60747-5-5 \(VDE 0884\)](#), available with option 1
- [BSI EN 62368-1](#)
- [CQC GB4943.1-2011](#)
- [CQC GB8898-2011](#)

### DESCRIPTION

The MOC8101, MOC8102, MOC8103, MOC8104 family optocoupler consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon planar phototransistor detector in a plastic plug-in DIP-6 package. The coupling device is suitable for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

The base terminal of the MOC8101, MOC8102, MOC8103, MOC8104 is not connected, resulting in a substantially improved common mode interference immunity.

### ORDERING INFORMATION



AGENCY CERTIFIED / PACKAGE	CTR (%)			
	10 mA			
<b>UL, cUL, BSI, CQC</b>	<b>50 to 80</b>	<b>73 to 117</b>	<b>108 to 173</b>	<b>160 to 256</b>
DIP-6	MOC8101	MOC8102	MOC8103	MOC8104
DIP-6, 400 mil, option 6	-	MOC8102-X006	-	-
SMD-6, option 9	-	MOC8102-X009 <sup>(1)</sup>	-	-
<b>UL, cUL, BSI, CQC, VDE (Option 1)</b>	<b>50 to 80</b>	<b>73 to 117</b>	<b>108 to 173</b>	<b>160 to 256</b>
DIP-6	-	-	MOC8103-X001	-
DIP-6, 400 mil	-	MOC8102-X016	-	MOC8104-X016
SMD-6, option 7	MOC8101-X017T	MOC8102-X017T <sup>(1)</sup>	-	-
SMD-6, option 9	-	-	-	MOC8104-X019T

### Notes

- Additional options may be possible, please contact sales office
- <sup>(1)</sup> Also available in tubes; do not put T on end



ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		V <sub>R</sub>	6.0	V
Forward continuous current		I <sub>F</sub>	60	mA
Surge forward current	t ≤ 10 μs	I <sub>FSM</sub>	2.5	A
Power dissipation		P <sub>diss</sub>	100	mW
Derate linearly from 25°C			1.33	mW/°C
<b>OUTPUT</b>				
Collector emitter breakdown voltage		BV <sub>CEO</sub>	30	V
Emitter collector breakdown voltage		BV <sub>ECO</sub>	7.0	V
Collector current		I <sub>C</sub>	50	mA
Derate linearly from 25°C			2.0	mW/°C
Power dissipation		P <sub>diss</sub>	150	mW
<b>COUPLER</b>				
Derate linearly from 25 °C			3.33	mW/°C
Total power dissipation		P <sub>tot</sub>	250	mW
Storage temperature		T <sub>stg</sub>	-55 to +150	°C
Operating temperature		T <sub>amb</sub>	-55 to +100	°C
Junction temperature		T <sub>j</sub>	100	°C
Soldering temperature <sup>(1)</sup>	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T <sub>slid</sub>	260	°C

**Notes**

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability
- <sup>(1)</sup> Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP)

ELECTRICAL CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	I <sub>F</sub> = 10 mA		V <sub>F</sub>	-	1.25	1.5	V
Breakdown voltage	I <sub>R</sub> = 10 μA		V <sub>BR</sub>	6.0	-	-	V
Reverse current	V <sub>R</sub> = 6.0 V		I <sub>R</sub>	-	0.01	10	μA
Capacitance	V <sub>R</sub> = 0 V, f = 1.0 MHz		C <sub>O</sub>	-	25	-	pF
Thermal resistance			R <sub>thja</sub>	-	750	-	K/W
<b>OUTPUT</b>							
Collector emitter capacitance	V <sub>CE</sub> = 5.0 V, f = 1.0 MHz		C <sub>CE</sub>	-	5.2	-	pF
Collector emitter dark current	V <sub>CE</sub> = 10 V, T <sub>amp</sub> = 25 °C	MOC8101	I <sub>CEO1</sub>	-	1.0	50	nA
	V <sub>CE</sub> = 10 V, T <sub>amp</sub> = 100 °C	MOC8102	I <sub>CEO1</sub>	-	1.0	-	μA
Collector emitter breakdown voltage	I <sub>C</sub> = 1.0 mA		BV <sub>CEO</sub>	30	-	-	V
Emitter collector breakdown voltage	I <sub>E</sub> = 100 μA		BV <sub>ECO</sub>	7.0	-	-	V
Thermal resistance			R <sub>thja</sub>	-	500	-	K/W
<b>COUPLER</b>							
Saturation voltage collector emitter	I <sub>F</sub> = 5.0 mA		V <sub>CEsat</sub>	-	0.25	0.4	V
Coupling capacitance			C <sub>C</sub>	-	0.6	-	pF

**Note**

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements